

# Gilberto Medeiros-Ribeiro

## List of Publications by Citations

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104  
g-index

173  
ext. papers

12,140  
ext. citations

5.5  
avg, IF

5.89  
L-index

#	Paper	IF	Citations
164	Shape transition of germanium nanocrystals on a silicon (001) surface from pyramids to domes. <i>Science</i> , <b>1998</b> , 279, 353-5	33.3	781
163	A scalable neuristor built with Mott memristors. <i>Nature Materials</i> , <b>2013</b> , 12, 114-7	27	614
162	Intermixing and shape changes during the formation of InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 2014-2016	3.4	528
161	Memristor-CMOS hybrid integrated circuits for reconfigurable logic. <i>Nano Letters</i> , <b>2009</b> , 9, 3640-5	11.5	507
160	Sub-nanosecond switching of a tantalum oxide memristor. <i>Nanotechnology</i> , <b>2011</b> , 22, 485203	3.4	506
159	High switching endurance in TaOx memristive devices. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 232102	3.4	467
158	Anatomy of a nanoscale conduction channel reveals the mechanism of a high-performance memristor. <i>Advanced Materials</i> , <b>2011</b> , 23, 5633-40	24	338
157	Charged Excitons in Self-Assembled Semiconductor Quantum Dots. <i>Physical Review Letters</i> , <b>1997</b> , 79, 5282-5285	7.4	282
156	Direct identification of the conducting channels in a functioning memristive device. <i>Advanced Materials</i> , <b>2010</b> , 22, 3573-7	24	278
155	Self-assembled growth of epitaxial erbium disilicide nanowires on silicon (001). <i>Applied Physics Letters</i> , <b>2000</b> , 76, 4004-4006	3.4	239
154	Shell structure and electron-electron interaction in self-assembled InAs quantum dots. <i>Europhysics Letters</i> , <b>1996</b> , 36, 197-202	1.6	238
153	Coulomb interactions in small charge-tunable quantum dots: A simple model. <i>Physical Review B</i> , <b>1998</b> , 58, 16221-16231	3.3	237
152	Few-electron ground states of charge-tunable self-assembled quantum dots. <i>Physical Review B</i> , <b>1997</b> , 56, 6764-6769	3.3	221
151	Evolution of Ge islands on Si(001) during annealing. <i>Journal of Applied Physics</i> , <b>1999</b> , 85, 1159-1171	2.5	221
150	Electron and hole energy levels in InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 1767-1769	3.4	188
149	Carrier relaxation and electronic structure in InAs self-assembled quantum dots. <i>Physical Review B</i> , <b>1996</b> , 54, 11346-11353	3.3	183
148	Anisotropy of the Raman spectra of nanographite ribbons. <i>Physical Review Letters</i> , <b>2004</b> , 93, 047403	7.4	177

147	Inverse Bloch oscillator: Strong terahertz-photocurrent resonances at the Bloch frequency. <i>Physical Review Letters</i> , <b>1996</b> , 76, 2973-2976	7.4	168
146	Engineering nonlinearity into memristors for passive crossbar applications. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 113501	3.4	162
145	3D composition of epitaxial nanocrystals by anomalous X-ray diffraction: observation of a Si-rich core in Ge domes on Si(100). <i>Physical Review Letters</i> , <b>2003</b> , 91, 176101	7.4	154
144	Metal/TiO <sub>2</sub> interfaces for memristive switches. <i>Applied Physics A: Materials Science and Processing</i> , <b>2011</b> , 102, 785-789	2.6	128
143	Individual and Collective Electronic Properties of Ag Nanocrystals. <i>Journal of Physical Chemistry B</i> , <b>1999</b> , 103, 10341-10347	3.4	124
142	State Dynamics and Modeling of Tantalum Oxide Memristors. <i>IEEE Transactions on Electron Devices</i> , <b>2013</b> , 60, 2194-2202	2.9	120
141	Aharonov-Bohm signature for neutral polarized excitons in type-II quantum dot ensembles. <i>Physical Review Letters</i> , <b>2004</b> , 92, 126402	7.4	118
140	Sketched oxide single-electron transistor. <i>Nature Nanotechnology</i> , <b>2011</b> , 6, 343-7	28.7	103
139	Polarization-selective excitation of nitrogen vacancy centers in diamond. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	102
138	Continuous electrical tuning of the chemical composition of TaO(x)-based memristors. <i>ACS Nano</i> , <b>2012</b> , 6, 2312-8	16.7	100
137	Single-electron charging and Coulomb interaction in InAs self-assembled quantum dot arrays. <i>Physical Review B</i> , <b>1997</b> , 55, 1568-1573	3.3	99
136	Diffusion of adhesion layer metals controls nanoscale memristive switching. <i>Advanced Materials</i> , <b>2010</b> , 22, 4034-8	24	95
135	Annealing of Ge nanocrystals on Si(001) at 550°C: Metastability of huts and the stability of pyramids and domes. <i>Physical Review B</i> , <b>1998</b> , 58, 3533-3536	3.3	95
134	The dynamics of tunneling into self-assembled InAs dots. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 2486-2488	3.4	94
133	Coexistence of memristance and negative differential resistance in a nanoscale metal-oxide-metal system. <i>Advanced Materials</i> , <b>2011</b> , 23, 1730-3	24	91
132	Direct evaluation of composition profile, strain relaxation, and elastic energy of Ge:Si(001) self-assembled islands by anomalous x-ray scattering. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	91
131	Dome-to-pyramid transition induced by alloying of Ge islands on Si(001). <i>Applied Physics A: Materials Science and Processing</i> , <b>1998</b> , 67, 727-730	2.6	87
130	Measuring the switching dynamics and energy efficiency of tantalum oxide memristors. <i>Nanotechnology</i> , <b>2011</b> , 22, 505402	3.4	85

129	The switching location of a bipolar memristor: chemical, thermal and structural mapping. <i>Nanotechnology</i> , <b>2011</b> , 22, 254015	3.4	82
128	Imaging and Spectroscopy of Single InAs Self-Assembled Quantum Dots using Ballistic Electron Emission Microscopy. <i>Physical Review Letters</i> , <b>1996</b> , 77, 5268-5271	7.4	79
127	Spectromicroscopy of tantalum oxide memristors. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 242114	3.4	77
126	Photoluminescence of charged InAs self-assembled quantum dots. <i>Physical Review B</i> , <b>1998</b> , 58, 3597-3600	3.3	77
125	Size quantization effects in InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 1727-1729	3.4	76
124	Assembly of submicrometre ferromagnets in gallium arsenide semiconductors. <i>Nature</i> , <b>1995</b> , 377, 707-710	3.4	76
123	InAs self-assembled quantum dots as controllable scattering centers near a two-dimensional electron gas. <i>Physical Review B</i> , <b>1998</b> , 58, 1506-1511	3.3	74
122	Three-Dimensional Carrier Confinement in Strain-Induced Self-Assembled Quantum Dots. <i>MRS Bulletin</i> , <b>1996</b> , 21, 50-54	3.2	71
121	Quantized conductance coincides with state instability and excess noise in tantalum oxide memristors. <i>Nature Communications</i> , <b>2016</b> , 7, 11142	17.4	69
120	Thermodynamics of coherently-strained $GexSi_{1-x}$ nanocrystals on Si(001): alloy composition and island formation. <i>Nano Letters</i> , <b>2007</b> , 7, 223-6	11.5	68
119	Equilibrium model of bimodal distributions of epitaxial island growth. <i>Physical Review Letters</i> , <b>2003</b> , 90, 146101	7.4	68
118	Structural and optical characterization of InAs/InGaAs self-assembled quantum dots grown on (311)B GaAs. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 3466-3470	2.5	66
117	Two- and Three-Terminal Resistive Switches: Nanometer-Scale Memristors and Memistors. <i>Advanced Functional Materials</i> , <b>2011</b> , 21, 2660-2665	15.6	64
116	Feedback write scheme for memristive switching devices. <i>Applied Physics A: Materials Science and Processing</i> , <b>2011</b> , 102, 973-982	2.6	63
115	Rehybridization of electronic structure in compressed two-dimensional quantum dot superlattices. <i>Physical Review B</i> , <b>1999</b> , 59, 1633-1636	3.3	63
114	Metal-Insulator Transition in a Disordered Two-Dimensional Electron Gas in GaAs-AlGaAs at Zero Magnetic Field. <i>Physical Review Letters</i> , <b>1999</b> , 82, 996-999	7.4	63
113	Observation of two resistance switching modes in TiO <sub>2</sub> memristive devices electroformed at low current. <i>Nanotechnology</i> , <b>2011</b> , 22, 254007	3.4	62
112	Lognormal switching times for titanium dioxide bipolar memristors: origin and resolution. <i>Nanotechnology</i> , <b>2011</b> , 22, 095702	3.4	61

111	Magnetoluminescence studies of InyAl1-yAs self-assembled quantum dots in AlxGa1-xAs matrices. <i>Physical Review B</i> , <b>1996</b> , 53, 16458-16461	3.3	61
110	Morphological and electrical changes in TiO2 memristive devices induced by electroforming and switching. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2010</b> , 4, 16-18	2.5	59
109	Nitride memristors. <i>Applied Physics A: Materials Science and Processing</i> , <b>2012</b> , 109, 1-4	2.6	58
108	Dopant Control by Atomic Layer Deposition in Oxide Films for Memristive Switches. <i>Chemistry of Materials</i> , <b>2011</b> , 23, 123-125	9.6	56
107	A memristor-based nonvolatile latch circuit. <i>Nanotechnology</i> , <b>2010</b> , 21, 235203	3.4	56
106	Thermodynamics of the size and shape of nanocrystals: epitaxial Ge on Si(001). <i>Annual Review of Physical Chemistry</i> , <b>2000</b> , 51, 527-51	15.7	55
105	Characterization of electroforming-free titanium dioxide memristors. <i>Beilstein Journal of Nanotechnology</i> , <b>2013</b> , 4, 467-73	3	54
104	Structural and chemical characterization of TiO2 memristive devices by spatially-resolved NEXAFS. <i>Nanotechnology</i> , <b>2009</b> , 20, 485701	3.4	52
103	Landau tensor in semiconductor nanostructures. <i>Physical Review Letters</i> , <b>2006</b> , 97, 236402	7.4	48
102	Ordered arrays of rare-earth silicide nanowires on Si(001). <i>Journal of Crystal Growth</i> , <b>2003</b> , 251, 657-661	1.6	48
101	Magnetic properties and imaging of Mn-implanted GaAs semiconductors. <i>Journal of Applied Physics</i> , <b>1996</b> , 79, 5296	2.5	48
100	Electronic structure and transport measurements of amorphous transition-metal oxides: observation of Fermi glass behavior. <i>Applied Physics A: Materials Science and Processing</i> , <b>2012</b> , 107, 1-11	2.6	47
99	Spin splitting of the electron ground states of InAs quantum dots. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 4229-4231	3.4	46
98	Localization of lattice dynamics in low-angle twisted bilayer graphene. <i>Nature</i> , <b>2021</b> , 590, 405-409	50.4	46
97	Identification of two light-induced charge states of the oxygen vacancy in single-crystalline rutile TiO2. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	44
96	Charging dynamics of InAs self-assembled quantum dots. <i>Physical Review B</i> , <b>1997</b> , 56, 3609-3612	3.3	42
95	Storage of electrons and holes in self-assembled InAs quantum dots. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 1839-1841	3.4	42
94	Evolution of thermodynamic potentials in closed and open nanocrystalline systems: Ge-Si:Si(001) islands. <i>Physical Review Letters</i> , <b>2008</b> , 100, 226101	7.4	41

93	Size distribution of coherently strained InAs quantum dots. <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 4268-4275	3.5	40
92	Hybrid CMOS/memristor circuits <b>2010</b> ,		39
91	X-ray study of atomic ordering in self-assembled Ge islands grown on Si(001). <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	39
90	Equilibrium Shape Diagram for Strained Ge Nanocrystals on Si(001). <i>Journal of Physical Chemistry B</i> , <b>1998</b> , 102, 9605-9609	3.4	39
89	Luminescence quenching in InAs quantum dots. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 2946-2948	3.4	36
88	Alloying mechanisms for epitaxial nanocrystals. <i>Physical Review Letters</i> , <b>2007</b> , 98, 165901	7.4	33
87	Growth and evolution of epitaxial erbium disilicide nanowires on Si (001). <i>Applied Physics A: Materials Science and Processing</i> , <b>2002</b> , 75, 353-361	2.6	32
86	Graphene nanoribbon superlattices fabricated via He ion lithography. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 193114	3.4	29
85	Extended excitons and compact heliumlike biexcitons in type-II quantum dots. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	29
84	The incommensurate nature of epitaxial titanium disilicide islands on Si(001). <i>Surface Science</i> , <b>2000</b> , 457, 147-156	1.8	28
83	g-factor engineering and control in self-assembled quantum dots. <i>Applied Physics A: Materials Science and Processing</i> , <b>2003</b> , 77, 725-729	2.6	27
82	Titanium disilicide nanostructures: two phases and their surfaces. <i>Surface Science</i> , <b>1999</b> , 431, 116-127	1.8	27
81	Chemical Thermodynamics of the Size and Shape of Strained Ge Nanocrystals Grown on Si(001). <i>Accounts of Chemical Research</i> , <b>1999</b> , 32, 425-433	24.3	26
80	Electronic coupling effects in self-assembled InAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1998</b> , 2, 704-708	3	25
79	On the origin of the blueshift from type-II quantum dots emission using microphotoluminescence. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2743-2745	3.4	24
78	AC sense technique for memristor crossbar. <i>Electronics Letters</i> , <b>2012</b> , 48, 757	1.1	23
77	Microstrip resonators for electron paramagnetic resonance experiments. <i>Review of Scientific Instruments</i> , <b>2009</b> , 80, 075111	1.7	23
76	Electronic structure of nanometer-size quantum dots and quantum rings. <i>Microelectronic Engineering</i> , <b>1999</b> , 47, 95-99	2.5	23

75	Impact of geometry on the performance of memristive nanodevices. <i>Nanotechnology</i> , <b>2011</b> , 22, 254026	3.4	22
74	Optical and structural properties of InAsP ternary self-assembled quantum dots embedded in GaAs. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2953-2955	3.4	21
73	Coulomb-coupling in vertically aligned self-assembled InAs quantum dots. <i>Nanotechnology</i> , <b>1999</b> , 10, 14-18	3.4	20
72	Size Quantization and Zero Dimensional Effects in Self Assembled Semiconductor Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4068-4072	1.4	19
71	Atomic ordering dependence on growth method in Ge:Si(001) islands: Influence of surface kinetic and thermodynamic interdiffusion mechanisms. <i>Physical Review B</i> , <b>2010</b> , 82,	3.3	18
70	Absorptive and dispersive optical responses of excitons in a single quantum dot. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 123124	3.4	17
69	Revealing Quantitative 3D Chemical Arrangement on GeBi Nanostructures. <i>Journal of Physical Chemistry C</i> , <b>2009</b> , 113, 9018-9022	3.8	16
68	Luminescence spectroscopy of InAs self-assembled quantum dots. <i>Superlattices and Microstructures</i> , <b>1997</b> , 21, 259-266	2.8	16
67	Scanning tunneling microscopy of template-stripped Au surfaces and highly ordered self-assembled monolayers. <i>Langmuir</i> , <b>2008</b> , 24, 5984-7	4	16
66	Two-dimensional magnetoexcitons in type-II semiconductor quantum dots. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	15
65	Nanoscale lateral switchable rectifiers fabricated by local anodic oxidation. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 024511	2.5	14
64	Microstrip resonator for microwaves with controllable polarization. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 204103	3.4	14
63	Elastic energy mapping of epitaxial nanocrystals. <i>Applied Physics A: Materials Science and Processing</i> , <b>2005</b> , 80, 1211-1214	2.6	14
62	Influence of phosphine on Ge/Si(001) island growth by chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 4215-4224	2.5	13
61	The effect of the planar doping on the electrical transport properties at the Al:n-GaAs(100) interface: Ultrahigh effective doping. <i>Journal of Applied Physics</i> , <b>1993</b> , 73, 820-823	2.5	13
60	The diffuse behavior of the ferroelectric transition in poly(vinylidene fluoride-trifluoroethylene) copolymers. <i>Journal of Polymer Science, Part B: Polymer Physics</i> , <b>1994</b> , 32, 953-959	2.6	13
59	Control of Ge/Si intermixing during Ge island growth. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 053118	3.4	12
58	Dissipative dynamics of spins in quantum dots. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	12

57	X-ray diffraction mapping of strain fields and chemical composition of SiGe:Si(001) quantum dot molecules. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	11
56	Effect of phosphorus on Ge/Si(001) island formation. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 2220-2222	3.4	11
55	Equilibrium size distributions of clusters during strained epitaxial growth. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 67, 31-38	3.1	11
54	Band offsets in transition-metal oxide heterostructures. <i>Journal Physics D: Applied Physics</i> , <b>2013</b> , 46, 295303	3.0	10
53	Fine structure in the spectrum of the few-electron ground states of self-assembled quantum dots. <i>Physica B: Condensed Matter</i> , <b>1998</b> , 249-251, 257-261	2.8	10
52	Micro-photoluminescence of self-assembled quantum dots in the presence of an electron gas. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 12, 872-875	3	10
51	Seeding of InP islands on InAs quantum dot templates. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 6548-6550	2.5	10
50	Annealing of phosphorus-doped Ge islands on Si(001). <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 1562-1567	2.5	9
49	Magneto-optical properties of InAs monolayers and In <sub>y</sub> Al <sub>1-y</sub> As self-assembled quantum dots in Ga(Al)As matrices. <i>Physica B: Condensed Matter</i> , <b>1996</b> , 227, 378-383	2.8	9
48	Submicron fabrication by local anodic oxidation of germanium thin films. <i>Nanotechnology</i> , <b>2009</b> , 20, 345304	3.0	8
47	An optical study of self-assembled In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs quantum dots embedded in a two-dimensional electron gas. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 7994-7998	2.5	8
46	Transport properties of two-dimensional electron gases in Ga[Al]As heterostructures containing InAs self-assembled quantum dots. <i>Microelectronic Engineering</i> , <b>1999</b> , 47, 73-75	2.5	8
45	Electrical conductivity of HfO <sub>3</sub> acid type crystals at 1 kHz. <i>Solid State Communications</i> , <b>1995</b> , 93, 1013-1017	3.0	8
44	Quantum corrections to conductivity in graphene with vacancies. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2018</b> , 100, 40-44	3	7
43	Patterning graphene with a helium ion microscope: Observation of metal-insulator transition induced by disorder. <i>Physical Review B</i> , <b>2015</b> , 91,	3.3	7
42	Interband absorption on self-assembled InAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1998</b> , 2, 23-27	3	7
41	Field dependent carrier dynamics and charged excitons in InAs self-assembled quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1998</b> , 2, 627-631	3	7
40	Controlling alloy composition of InAsP self-assembled quantum dots embedded in GaAs. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 3051-3056	2.5	7



39	Twisted Bilayer Graphene: A Versatile Fabrication Method and the Detection of Variable Nanometric Strain Caused by Twist-Angle Disorder. <i>ACS Applied Nano Materials</i> , <b>2021</b> , 4, 1858-1866	5.6	7
38	Progress in CMOS-memristor integration <b>2011</b> ,		6
37	Charging dynamics in vertically aligned InAs quantum dots. <i>Materials Science and Technology</i> , <b>2002</b> , 18, 725-728	1.5	6
36	Photon assisted transport through semiconductor quantum structures in intense terahertz electric fields. <i>Physica B: Condensed Matter</i> , <b>1996</b> , 227, 367-372	2.8	6
35	Transport signatures of correlated disorder in a two-dimensional electron gas. <i>Europhysics Letters</i> , <b>2003</b> , 61, 674-680	1.6	5
34	InAs/InGaAs self-assembled quantum dots grown on (311)B GaAs by molecular beam epitaxy		5
33	Photoluminescence measurements of complex defects in Si-doped Al <sub>0.3</sub> Ga <sub>0.7</sub> As. <i>Journal of Applied Physics</i> , <b>1994</b> , 76, 8051-8054	2.5	5
32	Equilibrium Distributions and the Nanostructure Diagram for Epitaxial Quantum Dots. <i>Journal of Computational and Theoretical Nanoscience</i> , <b>2007</b> , 4, 335-347	0.3	5
31	The limits of near field immersion microwave microscopy evaluated by imaging bilayer graphene moiré patterns. <i>Nature Communications</i> , <b>2021</b> , 12, 2980	17.4	5
30	Intermixing during Ripening in GeSi Incoherent Epitaxial Nanocrystals. <i>Journal of Physical Chemistry C</i> , <b>2012</b> , 116, 901-907	3.8	4
29	X-RAY DIFFRACTION METHODS FOR STUDYING STRAIN AND COMPOSITION IN EPITAXIAL NANOSTRUCTURED SYSTEMS. <i>Materials and Energy</i> , <b>2011</b> , 211-279		4
28	Epitaxial Growth of Strained Nanocrystals. <i>Physica Status Solidi (B): Basic Research</i> , <b>2002</b> , 230, 443-450	1.3	4
27	Novel Approach for High-Resolution Elastic Behavior Assessment of Alloyed Strained Nanostructures. <i>Journal of Physical Chemistry C</i> , <b>2010</b> , 114, 12409-12415	3.8	3
26	Optical properties of type-I and II quantum dots. <i>Brazilian Journal of Physics</i> , <b>2004</b> , 34, 555-559	1.2	3
25	Effect of phosphorus on island formation. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 13, 974-977	3	3
24	Limits and Properties of Size Quantization Effects in InAs Self Assembled Quantum Dots. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 452, 275		3
23	Raman spectra of twisted bilayer graphene close to the magic angle. <i>2D Materials</i> , <b>2022</b> , 9, 025007	5.9	3
22	Reactive epitaxy of metallic hafnium silicide nanocrystals. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 013107	3.4	2

21	Determination of spin polarization in InAs/GaAs self-assembled quantum dots. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 132106	3.4	2
20	Excited states in InAs self-assembled quantum dots <b>1996</b> , 2694, 185		2
19	Observation of moiré superlattices on twisted bilayer graphene by scanning microwave impedance microscopy <b>2020</b> ,		2
18	Size and Shape of Epitaxial Nanostructures <b>2003</b> , 81-93		2
17	Quasistatic and Pulse Measuring Techniques <b>2016</b> , 341-362		1
16	Designing memristors: Physics, materials science and engineering <b>2012</b> ,		1
15	TEM study of InAs self-assembled quantum dots in GaAs. <i>Thin Solid Films</i> , <b>1998</b> , 336, 38-41	2.2	1
14	Magneto-optics from type-II single quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2004</b> , 1, 543-546		1
13	Nanoscience and Nanotechnology Research at the Brazilian National Synchrotron Laboratory (LNLS). <i>Physica Status Solidi (B): Basic Research</i> , <b>2002</b> , 232, 24-31	1.3	1
12	Magnetic field dependence of the metal-insulator transition in Ga[Al]As-heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2000</b> , 6, 264-267	3	1
11	DX-center energy level dependence on silicon doping concentration in Al <sub>0.3</sub> Ga <sub>0.7</sub> As. <i>Journal of Electronic Materials</i> , <b>1995</b> , 24, 907-912	1.9	1
10	Oxide Based Memristive Nanodevices <b>2014</b> , 219-256		1
9	Assessing electronic states of InAsP/GaAs self-assembled quantum dots by photoluminescence and modulation spectroscopy. <i>Journal of Luminescence</i> , <b>2019</b> , 206, 639-644	3.8	1
8	Prediction-free, real-time flexible control of tidal lagoons through Proximal Policy Optimisation: A case study for the Swansea Lagoon. <i>Ocean Engineering</i> , <b>2022</b> , 247, 110657	3.9	0
7	Probing microwave capacitance of self-assembled quantum dots. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 032103	3.4	1
6	Chemical Nano-tomography of Self-assembled Ge-Si:Si(001) Islands from Quantitative High Resolution Transmission Electron Microscopy. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1184, 111		1
5	Technical Report: Industrial Research and Innovation at the Brazilian Synchrotron Light Laboratory. <i>Synchrotron Radiation News</i> , <b>2007</b> , 20, 13-18	0.6	1
4	Transport signatures for correlated disorder in self-assembled InAs quantum dots on GaAs. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 12, 591-594	3	1

- 3 Anomalous X-Ray Scattering On Self-Assembled Islands: Direct Evaluation Of Composition Profile, Strain Relaxation, And Elastic Energy. *Materials Research Society Symposia Proceedings*, **2002**, 737, 35
- 2 Growth and Capacitance Spectroscopy of Self Assembled Quantum Dots. *Materials Research Society Symposia Proceedings*, **1995**, 417, 221
- 1 Strong Terahertz-Photocurrent Resonances in Miniband Superlattices at the Bloch Frequency **1996**, 135-138